TVS Diode Arrays (SPA®Diodes)

General Purpose Surge Protection - SP1250

SP1250 50A Discrete Unidirectional TVS Diode



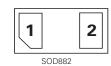






Note: This package image is for example and reference only. for detail package drawing, please refer to the package section in this datasheet

Pinout



Functional Block Diagram



Description

The SP1250 unidirectional TVS is fabricated in a proprietary silicon avalanche technology. These diodes provide a high ESD (electrostatic discharge) protection level for electronic equipment. The SP1250 TVS can safely absorb repetitive ESD strikes of ±30 kV (contact and air discharge as defined in IEC 61000-4-2) without any performance degradation. Additionally, each TVS can safely dissipate a 50A 8/20µs surge event as defined in IEC 61000-4-5 2nd edition.

Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 50A (8/20µs as defined in IEC 61000-4-5 2nd edition)
- Low leakage current of 0.02µA (TYP) at 5V
- Halogen free, lead free and RoHS compliant
- Moisture Sensitivity Level (MSL-1)
- AEC-Q101 Qualified

Applications

- VBUS Protection
- Portable Battery
- Switches / Buttons
- Test Equipment / Instrumentation
- Medical Equipment
- Notebooks / Desktops / Servers
- Computer Peripherals
- Point-of-Sale Terminals

Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated

TVS Diode Arrays (SPA®Diodes)

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I _{PP}	Peak Current (t _p =8/20µs)	50	А
T _{OP}	Operating Temperature	-40 to 125	°C
T _{STOR}	Storage Temperature	-55 to 150	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Electrical Characteristics (T_{OP}=25°C)

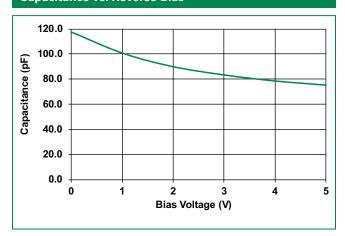
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R =1μA			5	V
Breakdown Voltage	V _{BR}	I _R =1mA	5.1	5.5		V
Reverse Leakage Current	I _{LEAK}	V _R =5V		0.02	0.1	μΑ
Clamp Voltage ¹	V _C	I _{pp} =50A, t _p =8/20μs		8.7	10	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p =100ns		0.05		Ω
ESD Withstand Voltage ¹	\/	IEC 61000-4-2 (Contact Discharge)	±30			kV
LOD Withstand Voltage	V _{ESD}	IEC 61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{IO-GND}	Reverse Bias=0V, f=1MHz		120		pF

Note:

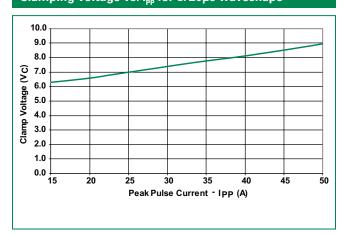
1. Parameter is guaranteed by design and/or component characterization.

2.Transmission Line Pulse (TLP) with 100ns width, 0.2ns rise time, and average window t1=70ns to t2= 90ns

Capacitance vs. Reverse Bias

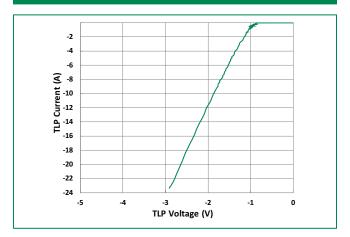


Clamping voltage vs. I_{pp} for 8/20µs waveshape

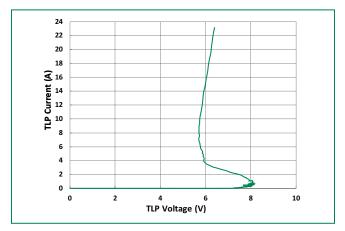




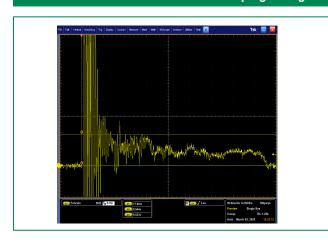
Negative Transmission Line Pulsing (TLP) Plot



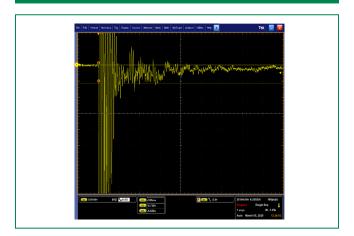
Positive Transmission Line Pulsing (TLP) Plot



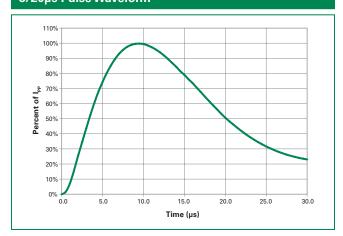
IEC 61000-4-2 +8 kV Contact ESD Clamping Voltage



IEC 61000-4-2 -8 kV Contact ESD Clamping Voltage



8/20µs Pulse Waveform





Soldering Parameters

Reflow Co	ndition	Pb – Free assembly	
	-Temperature Min (T _{s(min)})	150°C	
Pre Heat	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ra to peak	mp up rate (Liquidus) Temp (T _L)	3°C/second max	
$T_{S(max)}$ to T_{L}	- Ramp-up Rate	3°C/second max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
nellow	-Temperature (t _L)	60 – 150 seconds	
Peak Temp	erature (T _P)	260 ^{+0/-5} °C	
Time withi Temperatu	n 5°C of actual peak re (t _p)	20 – 40 seconds	
Ramp-dow	n Rate	6°C/second max	
Time 25°C to peak Temperature (T _P)		8 minutes Max.	
Do not exc	eed	260°C	

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$T_{S(max)}$ to T_L -	- Ramp-up Rate	3°C/second max	
Reflow	-Temperature (T _L) (Liquidus)	217°C	
nellow	-Temperature (t _L)	60 - 150 seconds	
Peak Tempe	erature (T _P)	260+0/-5 °C	
Time within 5°C of actual peak Temperature (t _p)		20 - 40 seconds	
Ramp-down Rate		6°C/second max	
Time 25°C	to peak Temperature (T _P)	8 minutes Max.	
Do not exceed		260°C	
	-		

Temperature ____ **T**P Critical Zone T_L to T_P Ramp-up T_L $\mathbf{T}_{\mathsf{S}(\mathsf{max})}$ Ramp-down Preheat $\textbf{T}_{\text{S}(\text{min})}$ time to peak temperature Time □

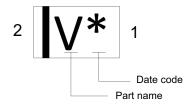
Product Characteristics

Lead Plating	Matte Tin		
Lead material	Copper Alloy		
Substrate Material	Silicon		
Body Material	Molded Compound		
Flammability	UL Recognized compound meeting flammability rating V-0		

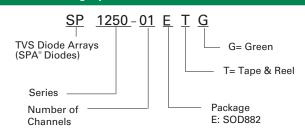
Ordering Information

Part Number	Package	Min. Order Qty.	
SP1250-01ETG	SOD882	10,000	

Part Marking System

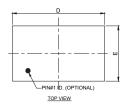


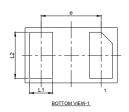
Part Numbering System



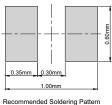


Package Dimensions — SOD882





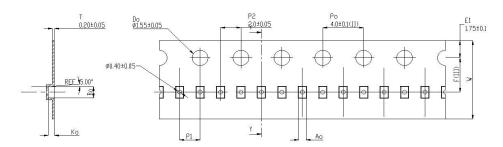




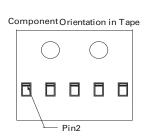
ecommended Soldering Patterr Drawing#: E03-B

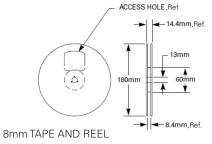
	SOD882					
Symbol	1	Millimeters		Inches		
	Min	Тур	Max	Min	Тур	Max
Α	0.40	0.50	0.55	0.016	0.020	0.022
A 1	0.00	0.02	0.05	0.000	0.001	0.002
L1	0.20	0.25	0.30	0.008	0.010	0.012
L2	0.45	0.50	0.55	0.018	0.020	0.022
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
е	0.65 BSC		(0.026 BSC		

Embossed Carrier Tape & Reel Specification — SOD882



Symbol	Millimeters		
A0	0.70+/-0.045		
В0	1.10+/-0.045		
K0	0.65+/-0.045		
F	3.50+/-0.05		
P1	2.00+/-0.10		
W	8.00 + 0.30 -0.10		





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